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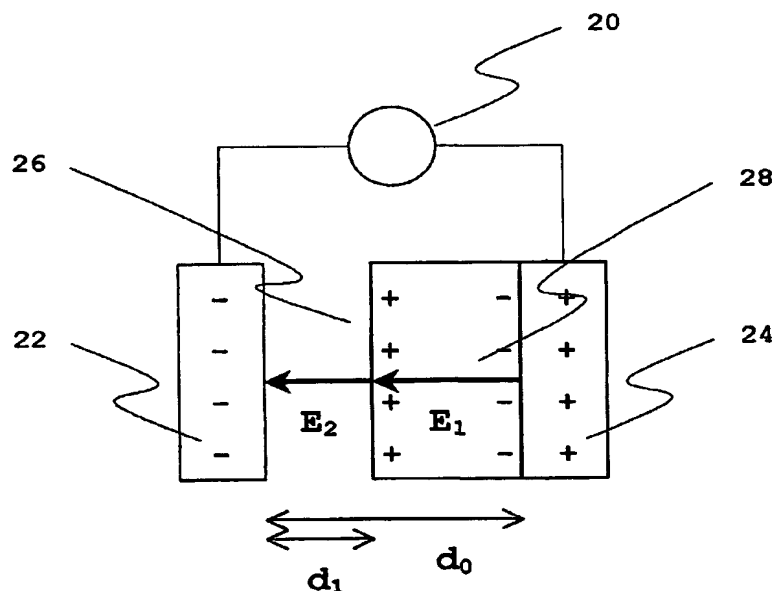
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(54) Title: METHOD FOR INCREASING EFFICIENCY OF THERMOTUNNEL DEVICES



(57) Abstract: The present invention comprises a tunneling device in which the collector electrode is modified so that tunneling of higher energy electrons from the emitter electrode to the collector electrode is enhanced. In one embodiment, the collector electrode is contacted with an insulator layer, preferably aluminum oxide, disposed between the collector and emitter electrodes. The present invention additionally comprises a method for enhancing tunneling of higher energy electrons from an emitter electrode to a collector electrode, the method comprising the step of contacting the collector electrode with an insulator, preferably aluminum oxide, and placing the insulator between the collector electrode and the emitter electrode.

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